

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claim 1 (currently amended): A surface emitting semiconductor laser chip, comprising:

a semiconductor body having, ~~at least partly,~~ a radiation exit face, a crystal structure ~~with~~ having principal crystal directions extending along a lateral direction of the radiation exit face, a ~~radiation exit face~~, and side faces laterally delimiting said semiconductor body, at least one of said side faces disposed obliquely with respect to ~~the~~ said principal crystal directions and perpendicularly with respect to said radiation exit face.

Claim 2 (original): The semiconductor laser chip according to claim 1, wherein said semiconductor body has a cross section selected from the group of square cross sections and rectangular cross sections disposed parallel to said radiation exit face.

Claim 3 (currently amended): The semiconductor laser chip according to claim 1, wherein at least one of said principal crystal directions extends ~~includes a given direction running~~ parallel to said radiation exit face, and at least one of said side faces forms an angle of between 40° and 50° with said at least one principal crystal ~~given~~ direction.

Claim 4 (original): The semiconductor laser chip according to claim 1, wherein said semiconductor body contains a substrate having, at least partly, a crystal structure.

Claim 5 (original): The semiconductor laser chip according to claim 4, wherein said semiconductor body contains a III-V compound semiconductor.

Claim 6 (original): The semiconductor laser chip according to claim 1, wherein the semiconductor laser chip is a VCSEL.

Claim 7 (original): The semiconductor laser chip according to claim 3, wherein said angle is 45°.

Claim 8 (original): The semiconductor laser chip according to claim 5, wherein said III-V compound semiconductor is selected from the group consisting of GaAs, AlGaAs, and a nitride compound semiconductor.

Claim 9 (currently amended): The semiconductor laser chip according to claim 1 ~~3~~, wherein said at least one principal crystal ~~given~~ direction is a [100] direction.

Claim 10 (withdrawn – previously presented): A method for producing a surface emitting semiconductor laser chip, which comprises the steps of:

producing a semiconductor wafer having a plurality of surface emitting semiconductor structures, the semiconductor wafer having principal crystal directions; and

dividing the semiconductor wafer into a plurality of semiconductor laser chips along separating line, the separating lines being disposed obliquely with respect to the principal crystal directions, each semiconductor laser chip having a radiation exit face and side faces laterally

delimiting the semiconductor body, at least one of the side faces disposed obliquely with respect to the principal crystal directions and perpendicularly with respect to the radiation exit face.

Claim 11 (withdrawn): The method according to claim 10, which further comprises performing the dividing step by one of sawing and etching the semiconductor wafer along the separating lines.

Claim 12 (withdrawn): The method according to claim 10, which further comprises creating the separating lines to form an angle of between 40° and 50° with the principal crystal directions.

Claim 13 (withdrawn): The method according to claim 10, which further comprises creating the separating lines to form an angle of 45° with the principal crystal directions.

Claim 14 (withdrawn): The method according to claim 10, which further comprises forming the semiconductor laser chips as vertical cavity surface emitting lasers.

Claim 15 (new): A surface emitting semiconductor laser chip, comprising:
a semiconductor body having a radiation exit face, a crystal structure having principal crystal directions extending along a lateral direction of the radiation exit face, and side faces laterally delimiting said semiconductor body, at least one of said side faces disposed obliquely with respect to said principal crystal directions, and wherein at least one of said principal crystal directions extends parallel to said radiation exit face and at least one of said side faces forms an angle of between 40° and 50° with said at least one principal crystal direction.